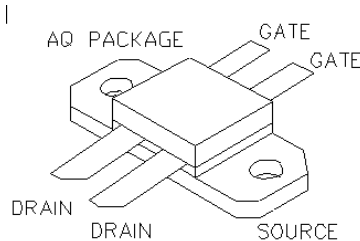




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features low feedback and output capacitances resulting in high F_t transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER VDMOS TRANSISTOR

90.0 Watts Push - Pull

Package Style AQ

**HIGH EFFICIENCY, LINEAR
HIGH GAIN, LOW NOISE**

ABSOLUTE MAXIMUM RATINGS ($T = 25^{\circ}\text{C}$)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
190 Watts	0.85°C/W	200°C	-65°C to 150°C	7.5 A	125V	125V	20 V

RF CHARACTERISTICS (90.0 WATTS OUTPUT)

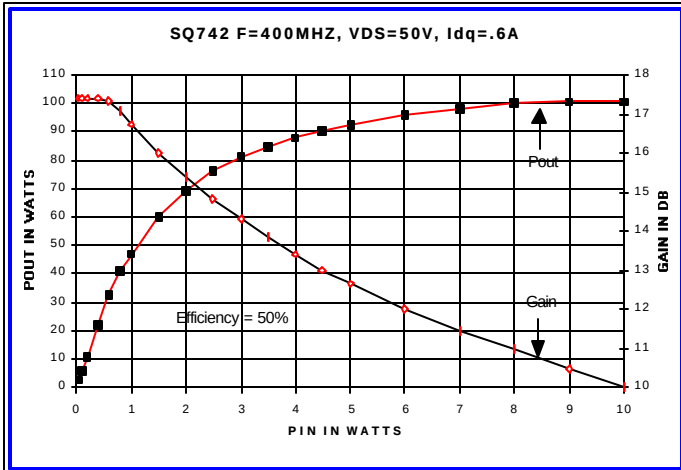
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	11			dB	$I_{dq} = 0.60\text{ A}$, $V_{ds} = 50.0\text{ V}$, $F = 400\text{ MHz}$
η	Drain Efficiency		50		%	$I_{dq} = 0.60\text{ A}$, $V_{ds} = 50.0\text{ V}$, $F = 400\text{ MHz}$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 0.60\text{ A}$, $V_{ds} = 50.0\text{ V}$, $F = 400\text{ MHz}$

ELECTRICAL CHARACTERISTICS (EACH SIDE)

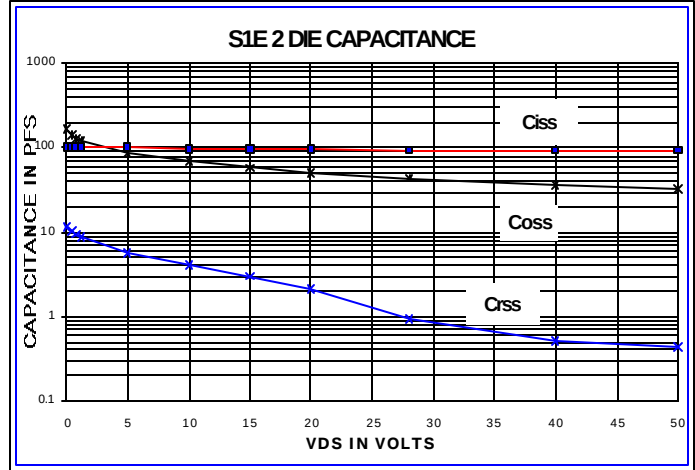
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	125			V	$I_{ds} = 20.00\text{ mA}$, $V_{gs} = 0\text{ V}$
Idss	Zero Bias Drain Current			2.0	mA	$V_{ds} = 50.0\text{ V}$, $V_{gs} = 0\text{ V}$
Igss	Gate Leakage Current			1	μA	$V_{ds} = 0\text{ V}$, $V_{gs} = 30\text{ V}$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.10\text{ A}$, $V_{gs} = V_{ds}$
gM	Forward Transconductance		1.6		Mho	$V_{ds} = 10\text{ V}$, $V_{gs} = 5\text{ V}$
Rdson	Saturation Resistance		1.50		Ohm	$V_{gs} = 20\text{ V}$, $I_{ds} = 2.00\text{ A}$
Idsat	Saturation Current		7.00		Amp	$V_{gs} = 20\text{ V}$, $V_{ds} = 10\text{ V}$
Ciss	Common Source Input Capacitance		96.0		pF	$V_{ds} = 50.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$
Crss	Common Source Feedback Capacitance		0.4		pF	$V_{ds} = 50.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$
Coss	Common Source Output Capacitance		34.0		pF	$V_{ds} = 50.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$

SQ742

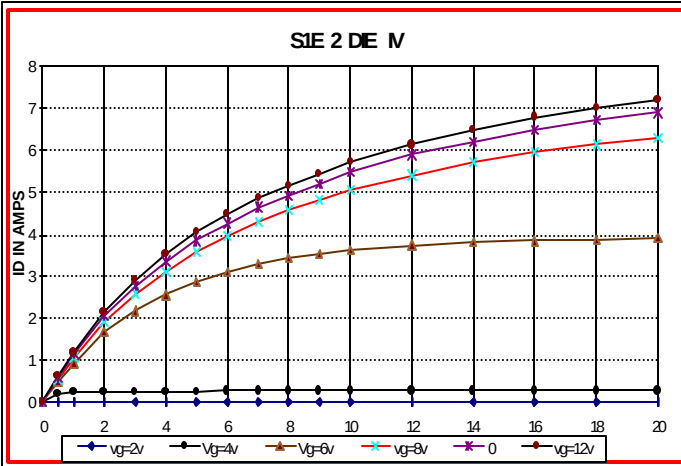
POUT VS PIN GRAPH



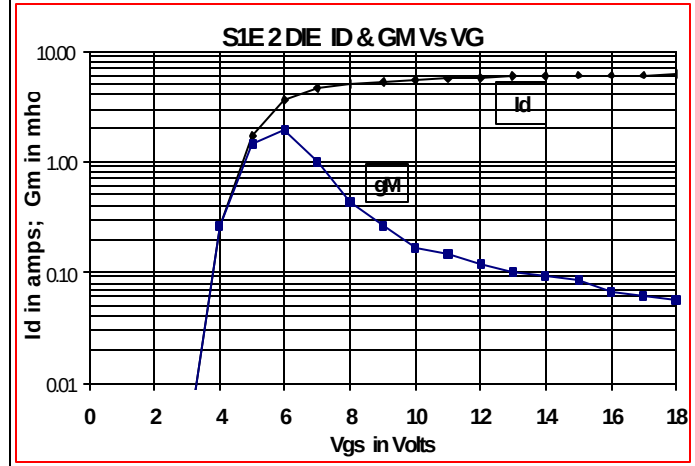
CAPACITANCE VS VOLTAGE



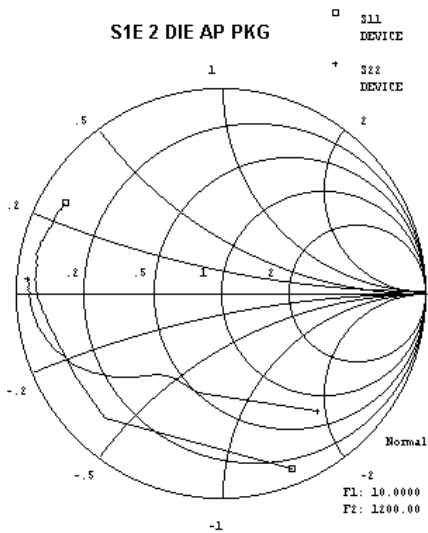
IV CURVE



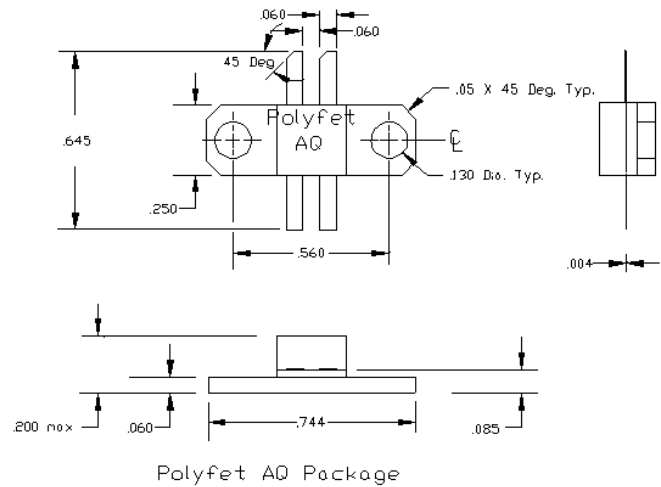
ID & GM VS VGS



S11 & S22 SMITH CHART



PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/-0.01 .XXX +/-0.005 inches

POLYFET RF DEVICES

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